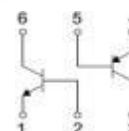
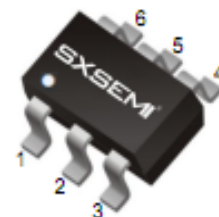


FEATURES

- Epitaxial Die Construction
- Two isolated NPN/PNP(BC847W+BC857W) Transistors in one package

SOT-363



MAKING: 7P

MAXIMUM RATINGS TR1 ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	50	V
V_{CEO}	Collector-Emitter Voltage	45	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current –Continuous	0.1	A
P_C	Collector Power Dissipation	200	mW
T_J, T_{stg}	Operation Junction and Storage Temperature Range	-55~+150	$^{\circ}\text{C}$

CHARACTERISTICS of TR1 (NPN Transistor) ($T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=10\mu\text{A}, I_E=0$	50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=10\text{mA}, I_B=0$	45			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=1\mu\text{A}, I_C=0$	6			V
Collector cut-off current	I_{CBO}	$V_{CB}=30\text{V}, I_E=0$			15	nA
Emitter cut-off current	I_{EBO}	$V_{EB}=5\text{V}, I_C=0$			15	nA
DC current gain	h_{FE}	$V_{CE}=5\text{V}, I_C=2\text{mA}$	200		450	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=10\text{mA}, I_B=0.5\text{mA}$			0.25	V
	$V_{CE(sat)}$	$I_C=100\text{mA}, I_B=5\text{mA}$			0.6	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=10\text{mA}, I_B=0.5\text{mA}$		0.7		V
	$V_{BE(sat)}$	$I_C=100\text{mA}, I_B=5\text{mA}$		0.9		V
Base-emitter voltage	$V_{BE(on)}$	$V_{CE}=5\text{V}, I_C=2\text{mA}$	0.58		0.7	V
	$V_{BE(on)}$	$V_{CE}=5\text{V}, I_C=10\text{mA}$			0.72	V
Collector output capacitance	C_{ob}	$V_{CB}=10\text{V}, I_E=0, f=1\text{MHz}$			6.0	pF
Transition frequency	f_T	$V_{CE}=5\text{V}, I_C=10\text{mA}, f=100\text{MHz}$	100			MHz
Noise figure	NF	$V_{CE}=5\text{V}, I_C=0.2\text{mA}, f=1\text{kHz}, R_g=2\text{K}\Omega, \Delta f=200\text{Hz}$			10	dB

MAXIMUM RATINGS TR2 ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-50	V
V_{CEO}	Collector-Emitter Voltage	-45	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current –Continuous	-0.1	A
P_C	Collector Power Dissipation	200	mW
T_J, T_{stg}	Operation Junction and Storage Temperature Range	-55~+150	$^{\circ}\text{C}$

CHARACTERISTICS of TR2 (PNP Transistor) ($T_a=25^{\circ}\text{C}$ unless otherwise specified)

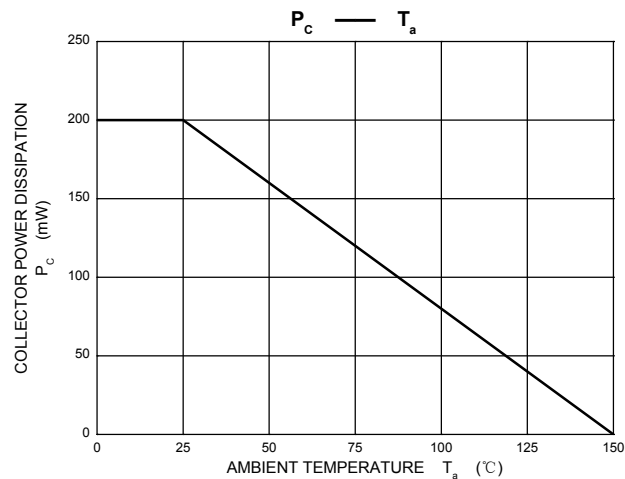
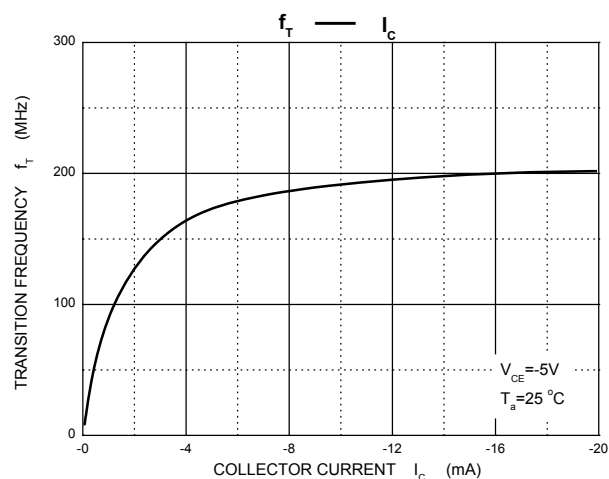
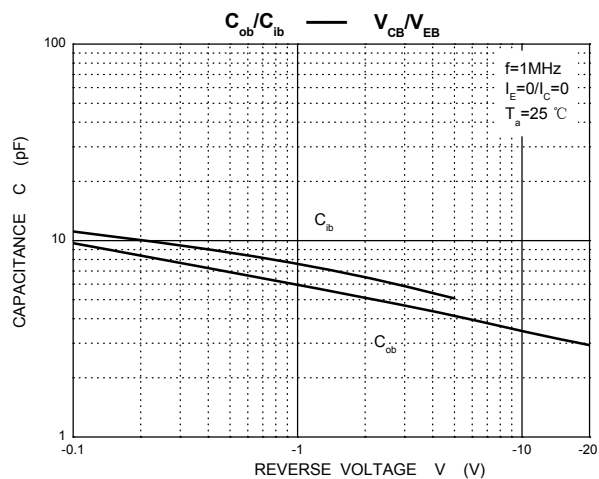
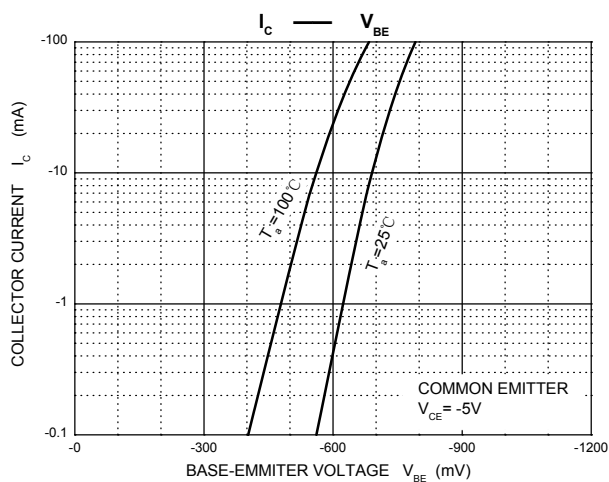
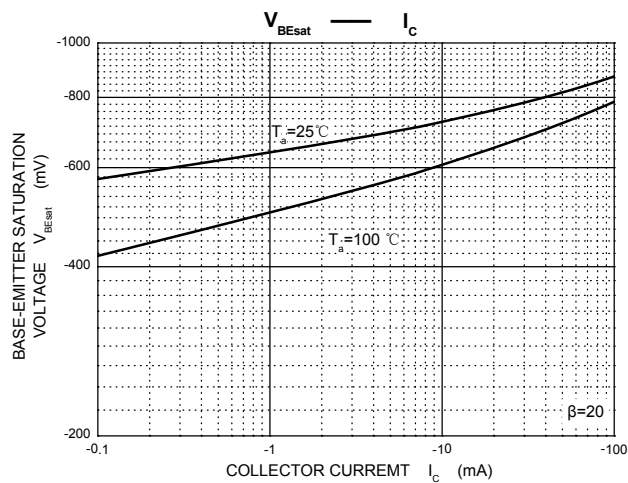
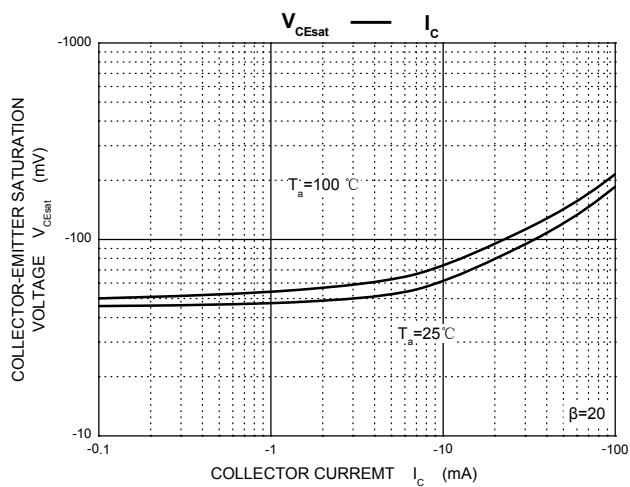
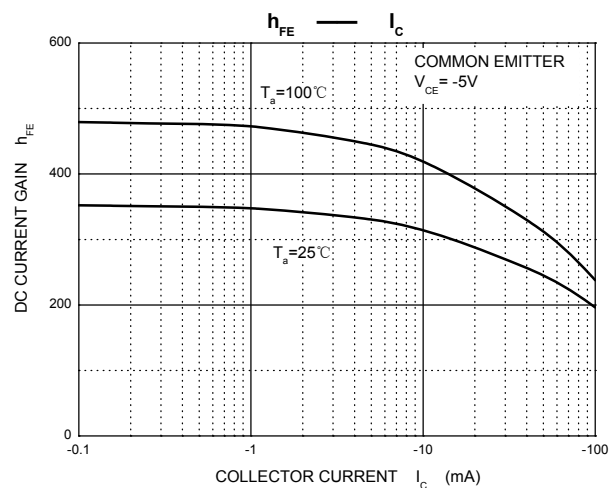
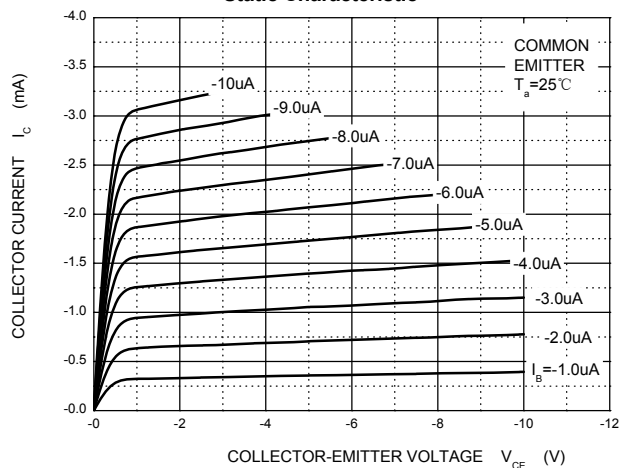
Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-10\mu\text{A}, I_E=0$	-50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-10\text{mA}, I_B=0$	-45			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-1\mu\text{A}, I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-30\text{V}, I_E=0$			-15	nA
Emitter cut-off current	I_{EBO}	$V_{EB}=-5\text{V}, I_C=0$			-15	nA
DC current gain	h_{FE1}	$V_{CE}=-5\text{V}, I_C=-2\text{mA}$	220		475	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-10\text{mA}, I_B=-0.5\text{mA}$			-0.3	V
	$V_{CE(sat)}$	$I_C=-100\text{mA}, I_B=-5\text{mA}$			-0.65	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=-10\text{mA}, I_B=-0.5\text{mA}$		-0.7		V
	$V_{BE(sat)}$	$I_C=-100\text{mA}, I_B=-5\text{mA}$			-0.95	V
Base-emitter voltage	$V_{BE(on)}$	$V_{CE}=-5\text{V}, I_C=-2\text{mA}$	-0.6		-0.75	V
	$V_{BE(on)}$	$V_{CE}=-5\text{V}, I_C=-10\text{mA}$			-0.82	V
Collector output capacitance	C_{ob}	$V_{CB}=-10\text{V}, I_E=0, f=1\text{MHz}$			4.5	pF
Transition frequency	f_T	$V_{CE}=-5\text{V}, I_C=-10\text{mA}, f=100\text{MHz}$	100			MHz
Noise figure	NF	$V_{CE}=-5\text{V}, I_C=-0.2\text{mA}, f=1\text{kHz}, R_g=2\text{K}\Omega, \Delta f=200\text{Hz}$			10	dB

Typical Characteristics

DUAL TRANSISTOR (NPN+PNP)

BC847PN/TR1

Static Characteristic

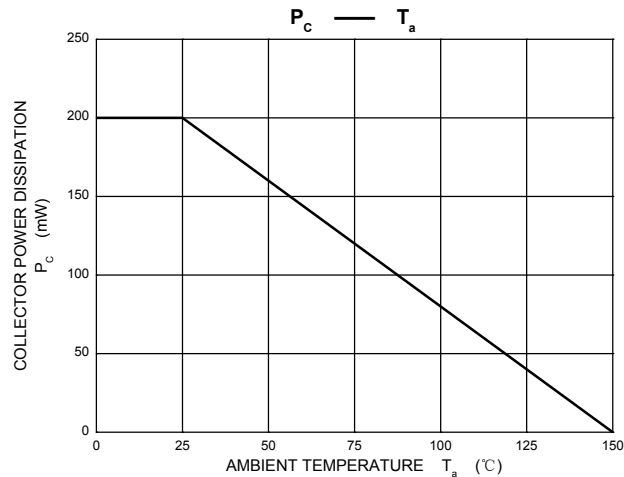
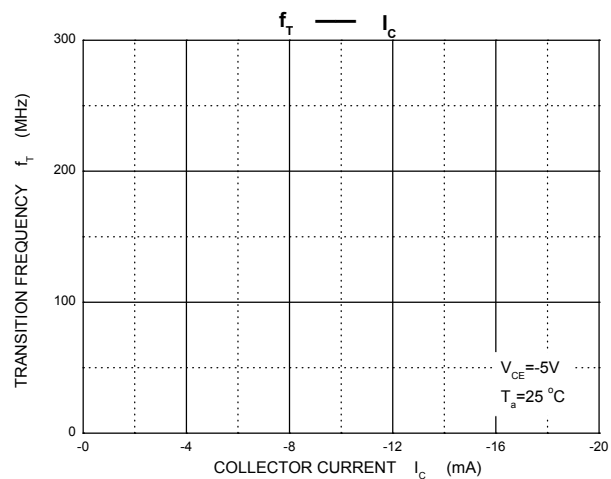
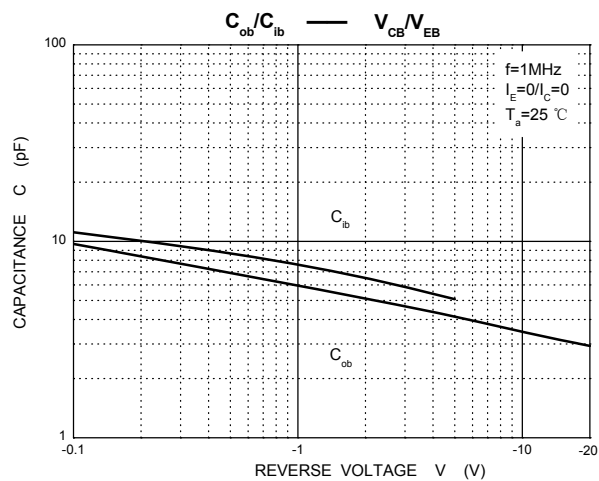
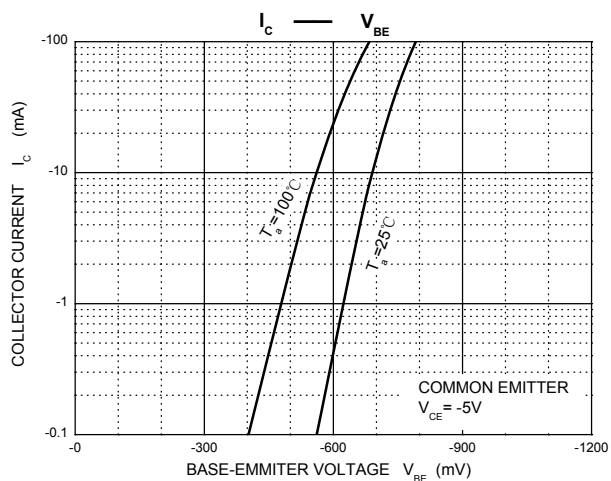
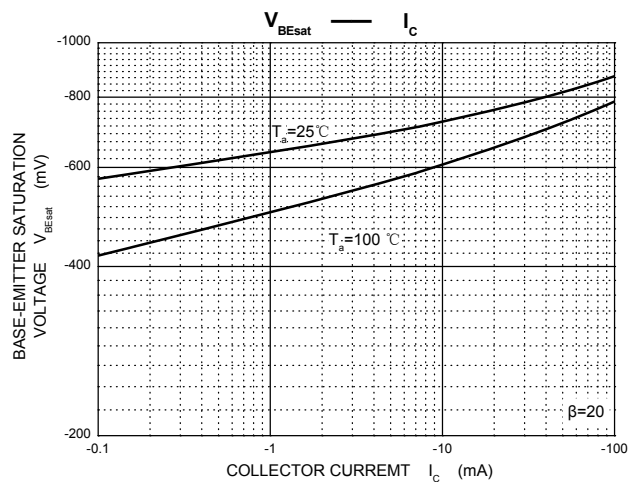
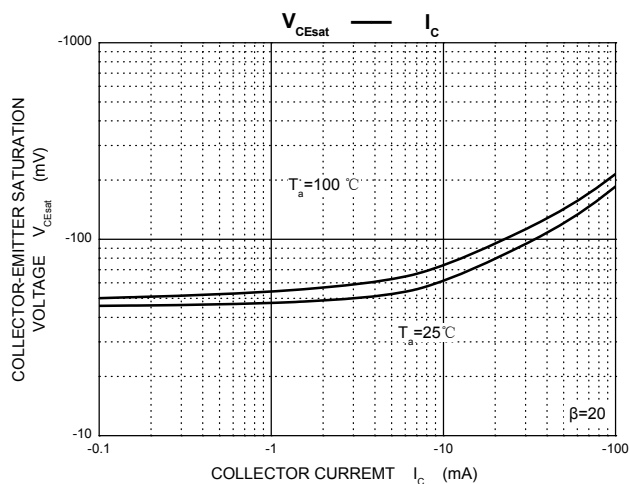
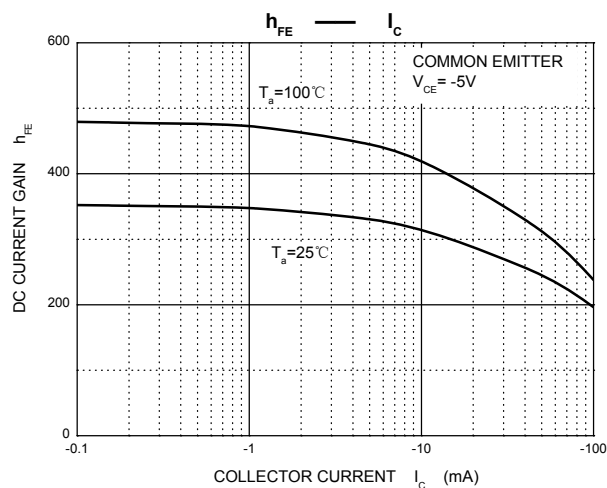
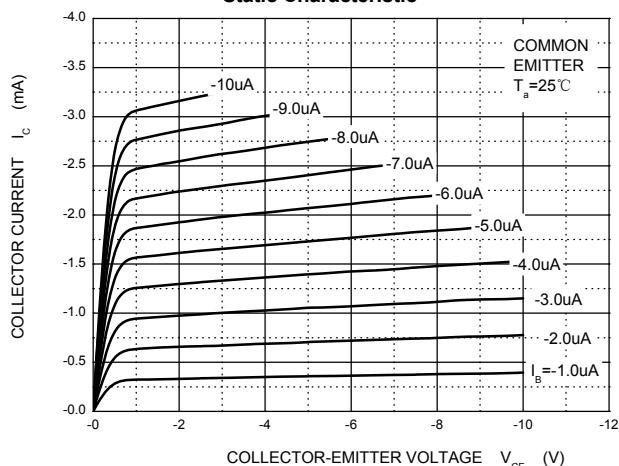


Typical Characteristics

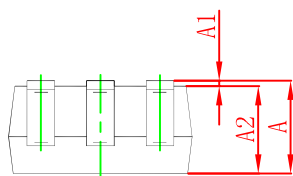
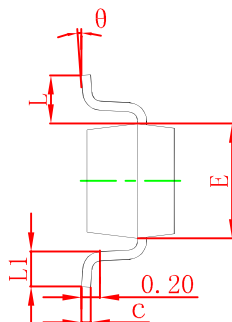
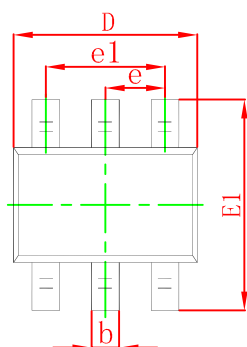
DUAL TRANSISTOR (NPN+PNP)

BC847PN/TR2

Static Characteristic

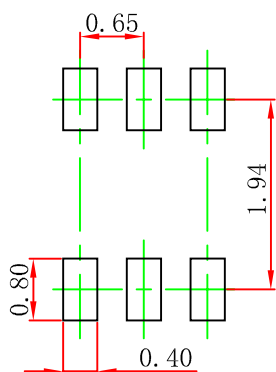


SOT-363 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.150	0.350	0.006	0.014
c	0.100	0.150	0.004	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.400	0.085	0.094
e	0.650 TYP		0.026 TYP	
e1	1.200	1.400	0.047	0.055
L	0.525 REF		0.021 REF	
L1	0.260	0.460	0.010	0.018
theta	0°	8°	0°	8°

SOT-363 Suggested Pad Layout



Note:

1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.05\text{mm}$.
3. The pad layout is for reference purposes only.